

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	0	method with semiconductor with lattice with implanting with precipitate with dynamic with defect with gate with noncontinuous.clms.	US-PGPUB	OR	ON	2008/01/06 19:36
L4	2431	438/149.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 19:40
L5	219	438/407.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 19:40
L6	213	438/423.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 19:40
L7	745	438/486.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 19:40
L8	97	438/139.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 19:40
L9	3522	I4 or I5 or I6 or I7 or I8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 19:41
S1	88	438/139.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/06 19:40
S2	540	438/486.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/19 15:10

## EAST Search History

S3	2	precipitate and (dynamic adj defect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/22 05:54
S4	2	precipitate and (dynamic adj defect) and crystal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/22 05:54
S5	5	"6593173"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/19 15:11
S6	8	"6395621"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/19 15:11